

BC846BDW1, BC847BDW1, BC848CDW1

Dual General Purpose Transistors

NPN Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

Features

- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	BC846	BC847	BC848	Unit
Collector-Emmitter Voltage	V_{CEO}	65	45	30	V
Collector-Base Voltage	V_{CBO}	80	50	30	V
Emitter-Base Voltage	V_{EBO}	6.0	6.0	5.0	V
Collector Current - Continuous	I_C	100	100	100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	380 250 3.0	mW mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C

1. FR-5 = 1.0 x 0.75 x 0.062 in

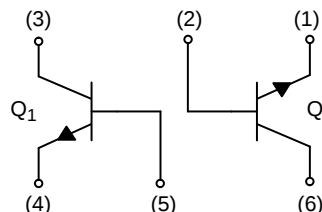


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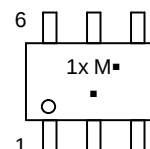
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SOT-363/SC-88
CASE 419B
STYLE 1



MARKING DIAGRAM



1x = Specific Device Code

x = B, F, G, L

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BC846BDW1, BC847BDW1, BC848CDW1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 10 mA) BC846 BC847 BC848	V _{(BR)CEO}	65 45 30	– – –	– – –	V
Collector – Emitter Breakdown Voltage (I _C = 10 µA, V _{EB} = 0) BC846 BC847 BC848	V _{(BR)CES}	80 50 30	– – –	– – –	V
Collector – Base Breakdown Voltage (I _C = 10 µA) BC846 BC847 BC848	V _{(BR)CBO}	80 50 30	– – –	– – –	V
Emitter – Base Breakdown Voltage (I _E = 1.0 µA) BC846 BC847 BC848	V _{(BR)EBO}	6.0 6.0 5.0	– – –	– – –	V
Collector Cutoff Current (V _{CB} = 30 V) (V _{CB} = 30 V, T _A = 150°C)	I _{CBO}	– –	– –	15 5.0	nA µA

ON CHARACTERISTICS

DC Current Gain (I _C = 10 µA, V _{CE} = 5.0 V) BC846B, BC847B BC847C, BC848C (I _C = 2.0 mA, V _{CE} = 5.0 V) BC846B, BC847B BC847C, BC848C	h _{FE}	– – 200 420	150 270 290 520	– – 450 800	–
Collector – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)	V _{CE(sat)}	– –	– –	0.25 0.6	V
Base – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)	V _{BE(sat)}	– –	0.7 0.9	– –	V
Base – Emitter Voltage (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V)	V _{BE(on)}	580 –	660 –	700 770	mV

SMALL – SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	100	–	–	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	–	–	4.5	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	–	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BC846BDW1, BC847BDW1, BC848CDW1

TYPICAL CHARACTERISTICS – BC846BDW1

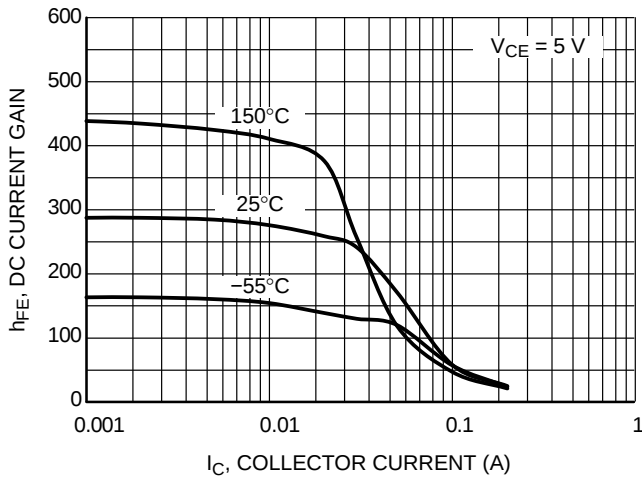


Figure 1. DC Current Gain at $V_{CE} = 5\text{ V}$

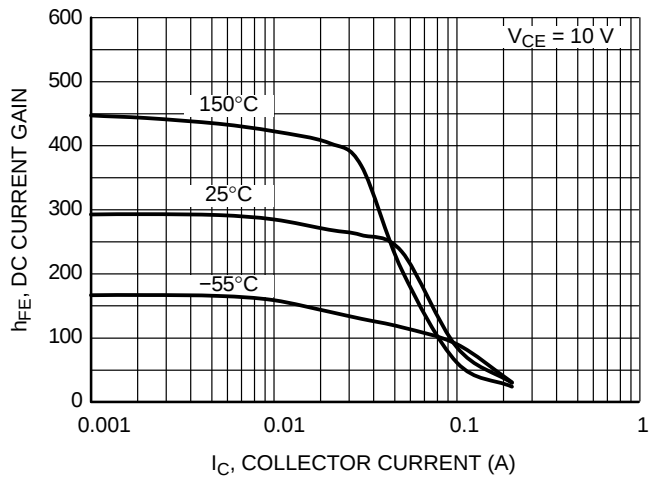


Figure 2. DC Current Gain at $V_{CE} = 10\text{ V}$

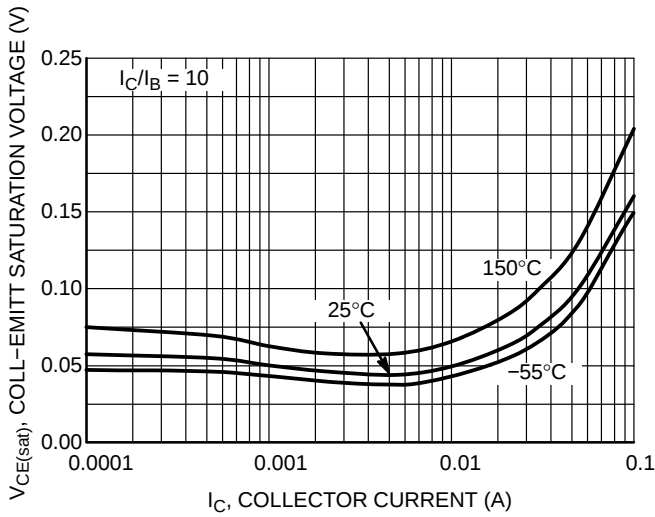


Figure 3. $V_{CE(sat)}$ at $I_C/I_B = 10$

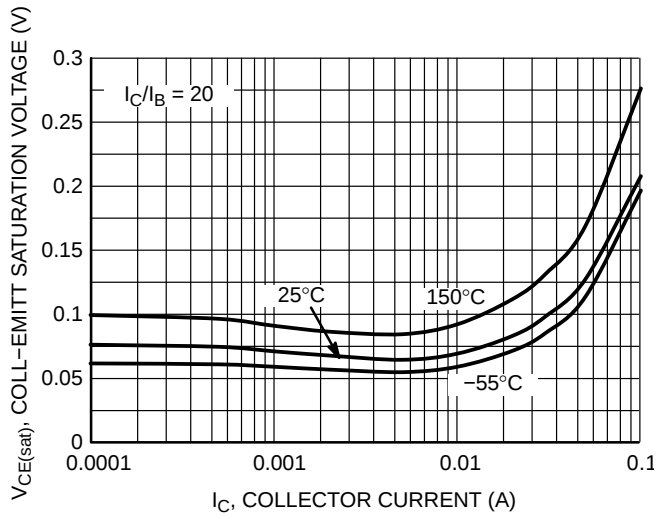


Figure 4. $V_{CE(sat)}$ at $I_C/I_B = 20$

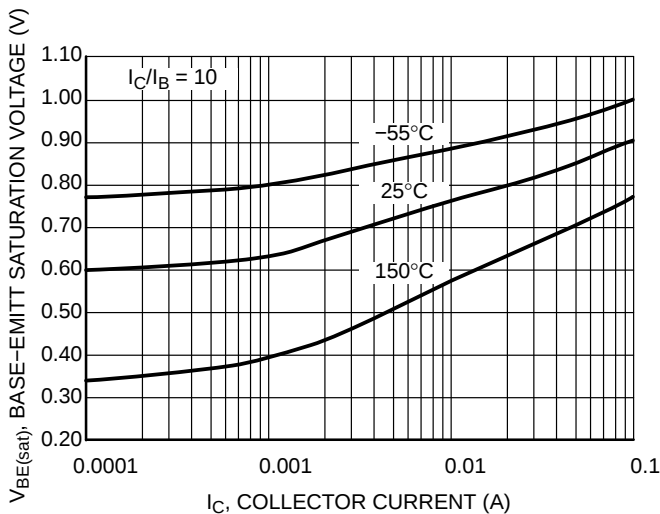


Figure 5. $V_{BE(sat)}$ at $I_C/I_B = 10$

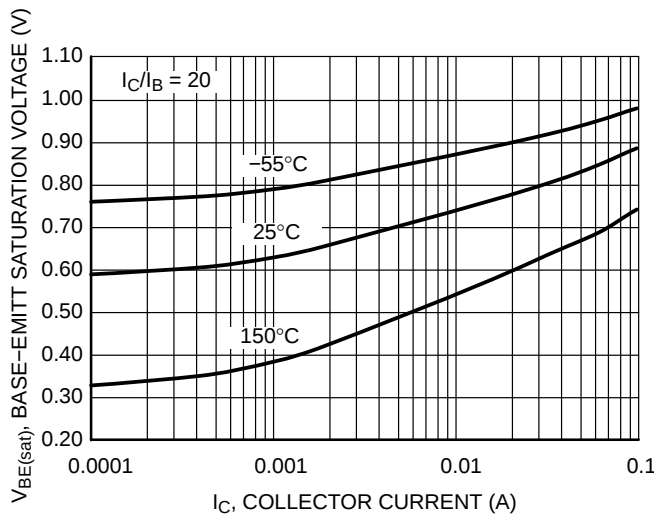


Figure 6. $V_{BE(sat)}$ at $I_C/I_B = 20$

BC846BDW1, BC847BDW1, BC848CDW1

TYPICAL CHARACTERISTICS – BC846BDW1

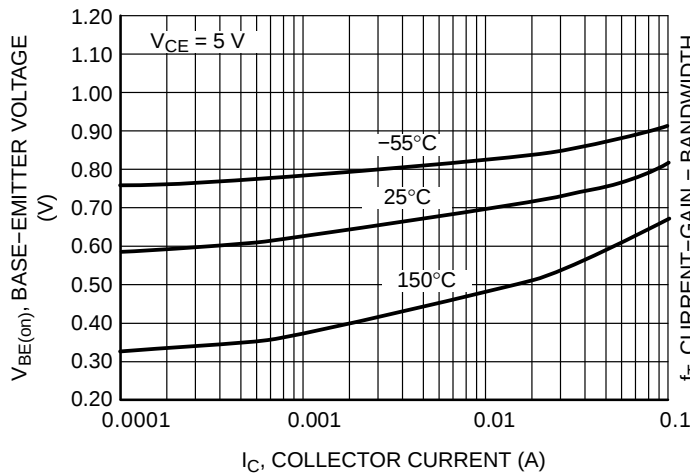


Figure 7. $V_{BE(on)}$ at $V_{CE} = 5\text{ V}$

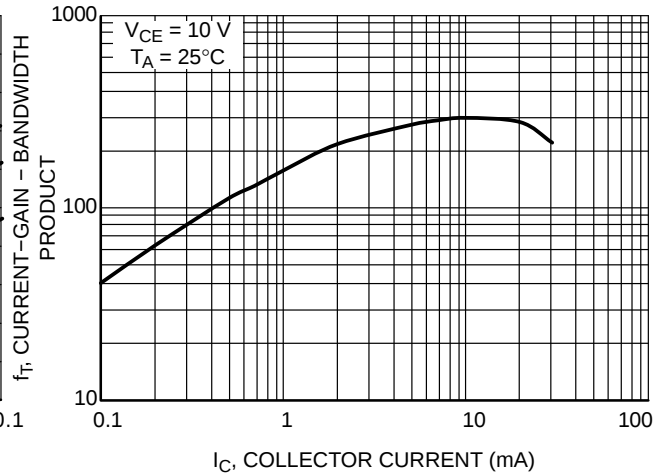


Figure 8. Current - Gain - Bandwidth Product

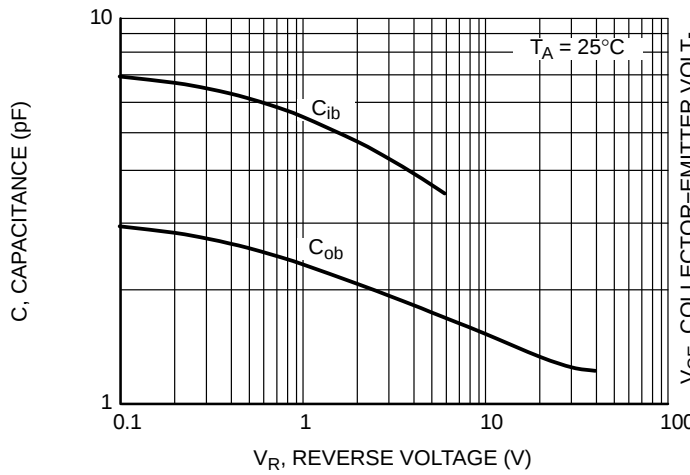


Figure 9. Capacitances

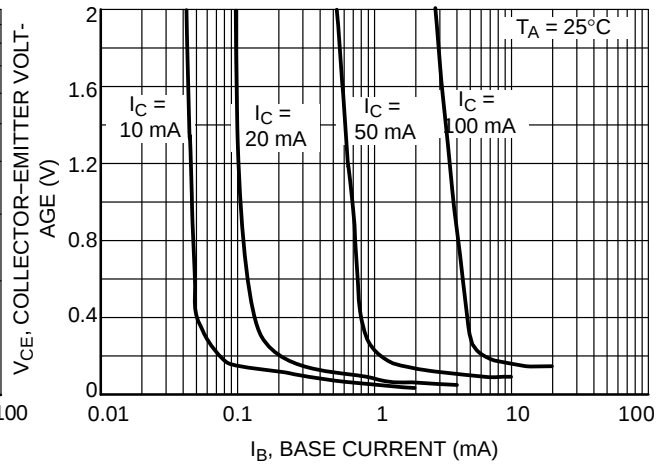


Figure 10. Collector Saturation Region

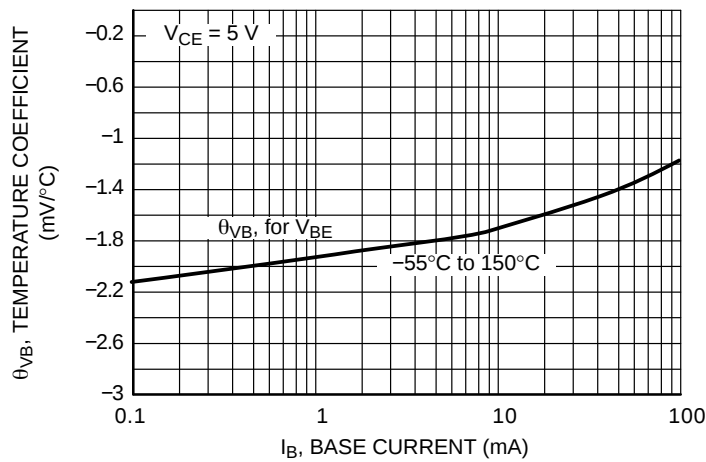


Figure 11. Base-Emitter Temperature Coefficient

BC846BDW1, BC847BDW1, BC848CDW1

TYPICAL CHARACTERISTICS – BC847BDW1

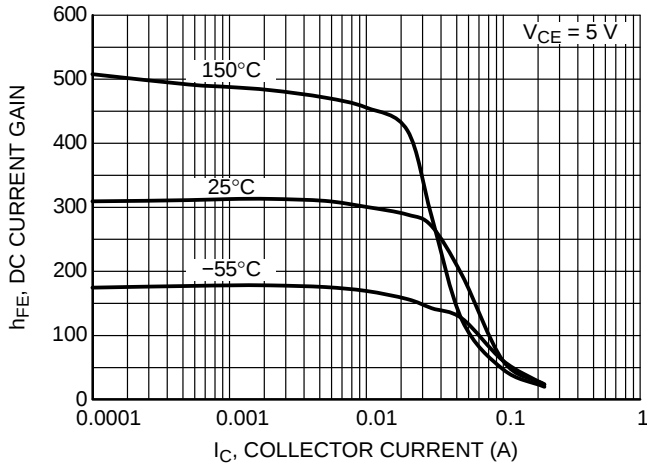


Figure 12. DC Current Gain at $V_{CE} = 5\text{ V}$

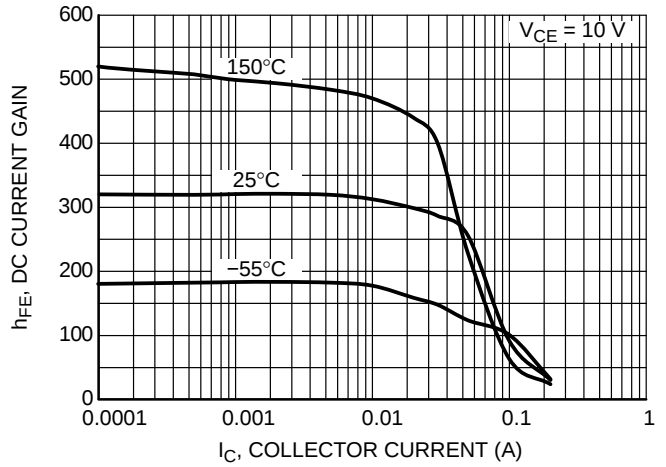


Figure 13. DC Current Gain at $V_{CE} = 10\text{ V}$

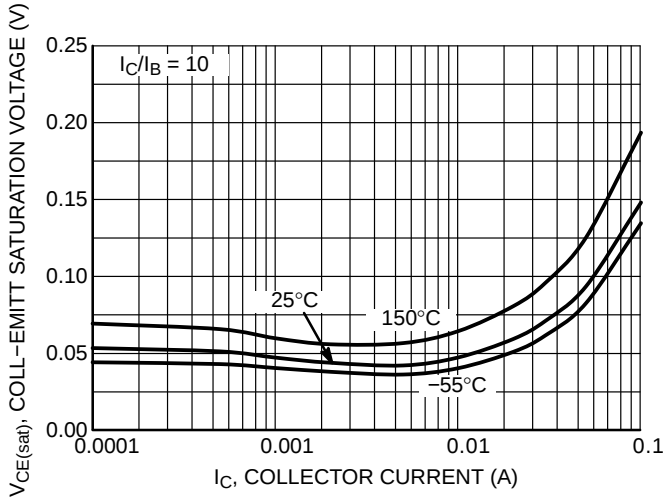


Figure 14. V_{CE} at $I_C/I_B = 10$

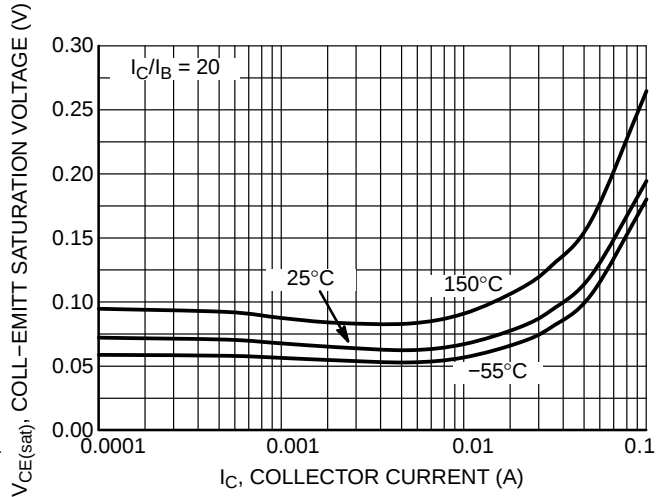


Figure 15. V_{CE} at $I_C/I_B = 20$

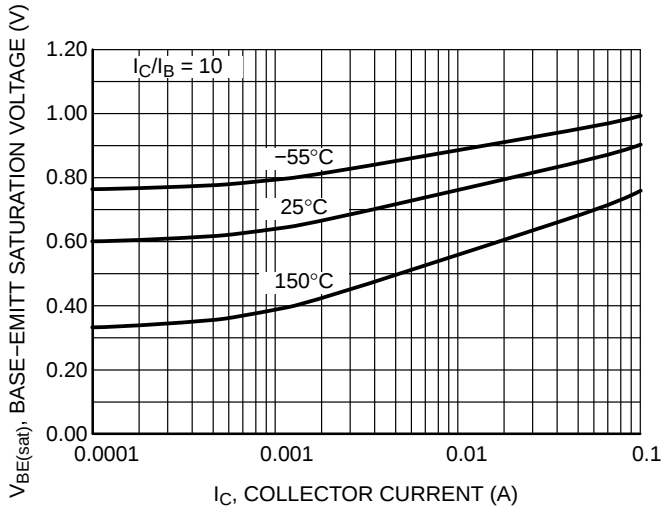


Figure 16. $V_{BE(sat)}$ at $I_C/I_B = 10$

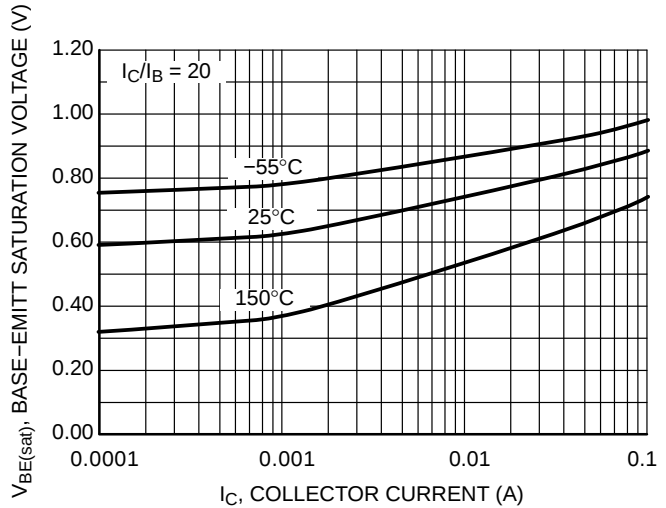


Figure 17. $V_{BE(sat)}$ at $I_C/I_B = 20$

BC846BDW1, BC847BDW1, BC848CDW1

TYPICAL CHARACTERISTICS – BC847BDW1

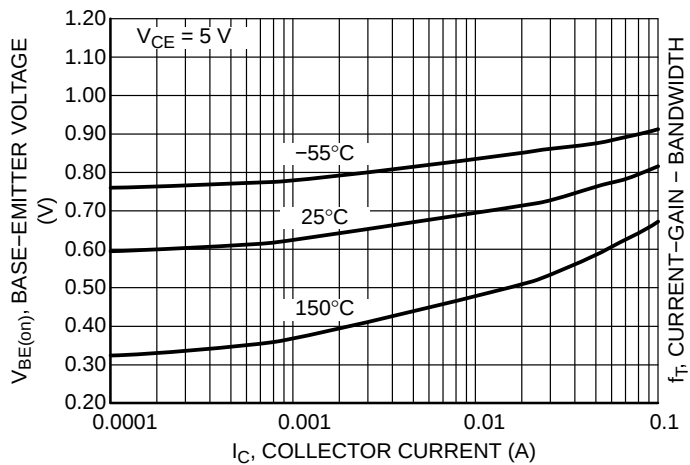


Figure 18. $V_{BE(on)}$ at $V_{CE} = 5\text{ V}$

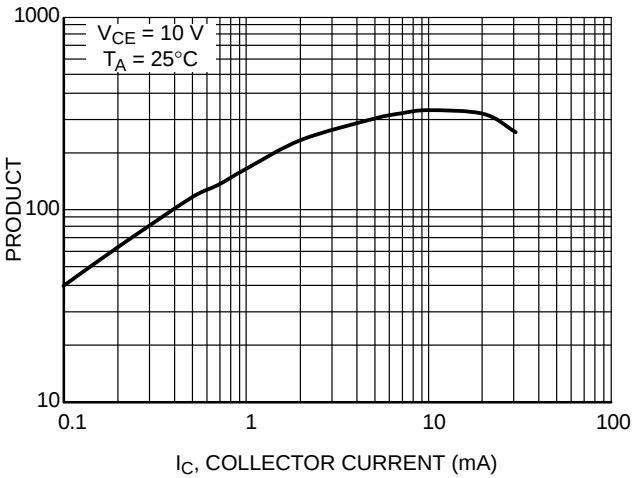


Figure 19. Current - Gain - Bandwidth Product

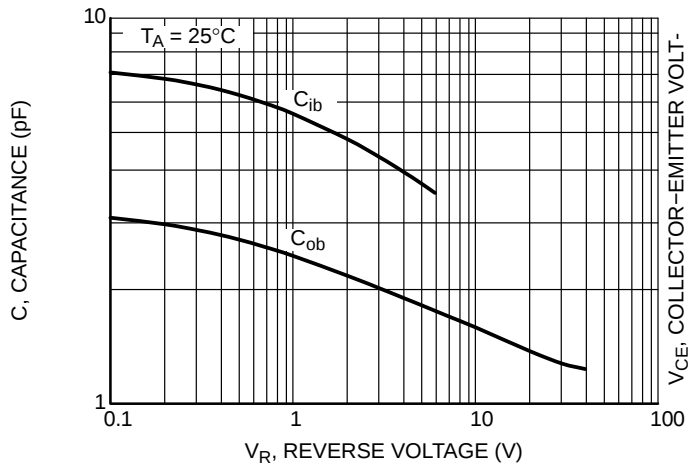


Figure 20. Capacitances

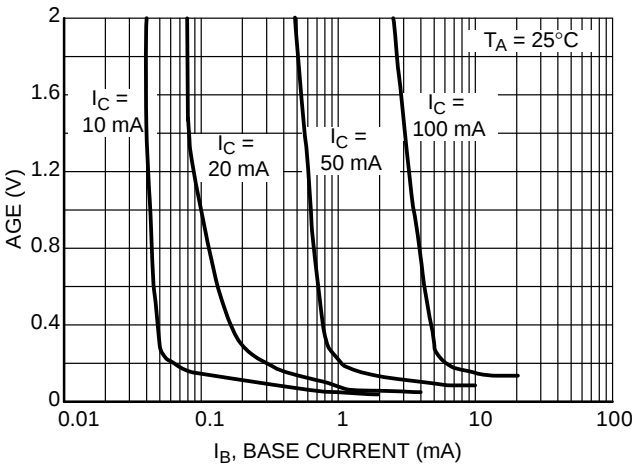


Figure 21. Collector Saturation Region

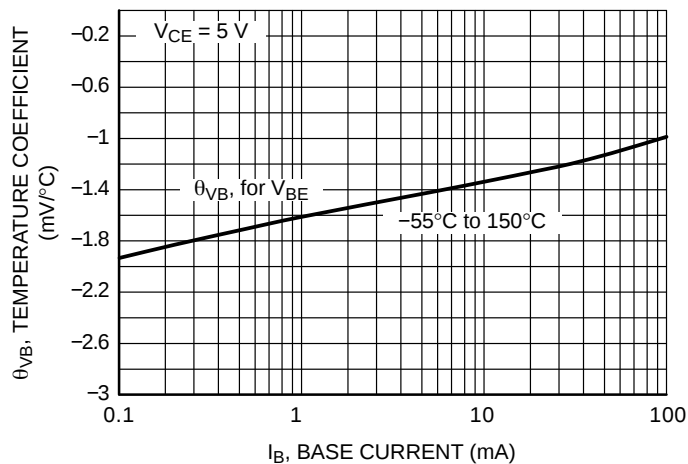


Figure 22. Base-Emitter Temperature Coefficient

TYPICAL CHARACTERISTICS – BC848CDW1

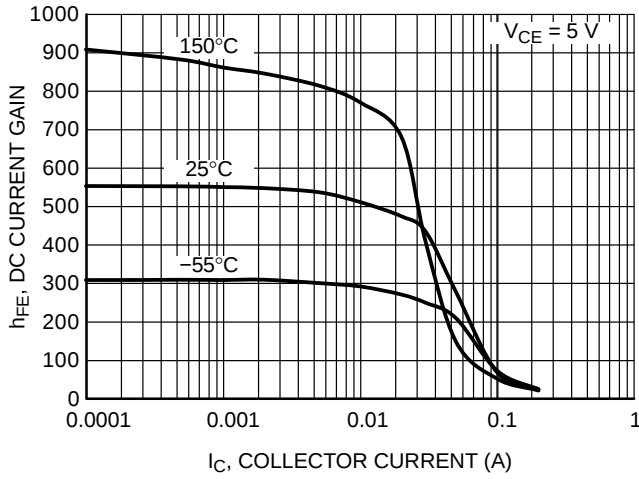


Figure 23. DC Current Gain at $V_{CE} = 5\text{ V}$

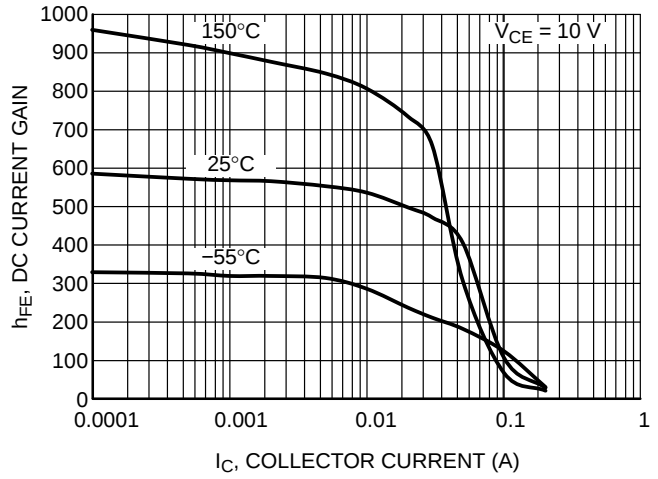


Figure 24. DC Current Gain at $V_{CE} = 10\text{ V}$

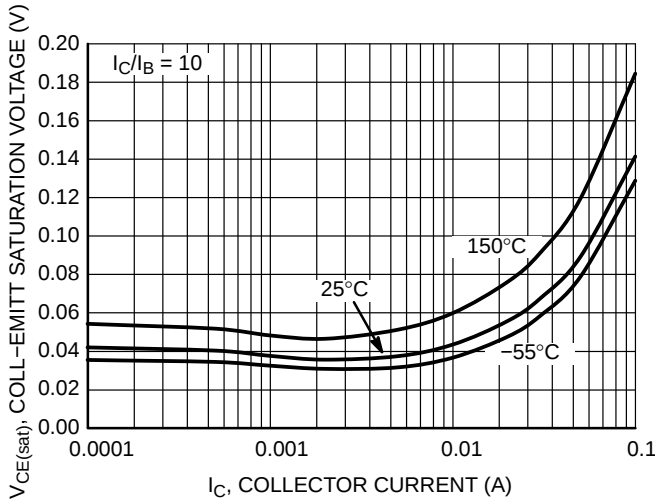


Figure 25. V_{CE} at $I_C/I_B = 10$

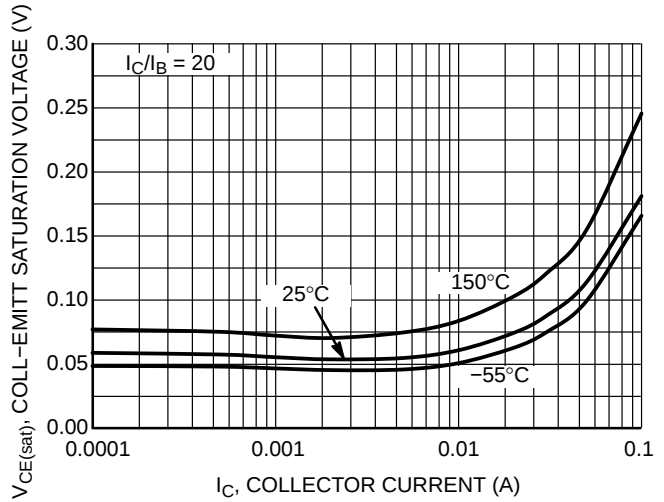


Figure 26. V_{CE} at $I_C/I_B = 20$

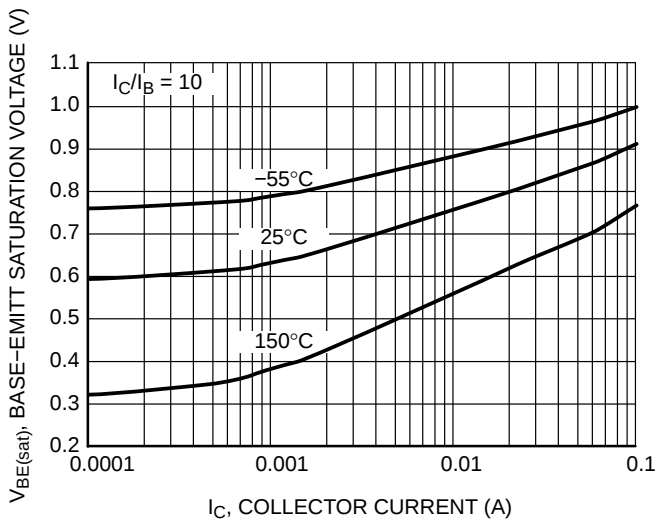


Figure 27. $V_{BE(sat)}$ at $I_C/I_B = 10$

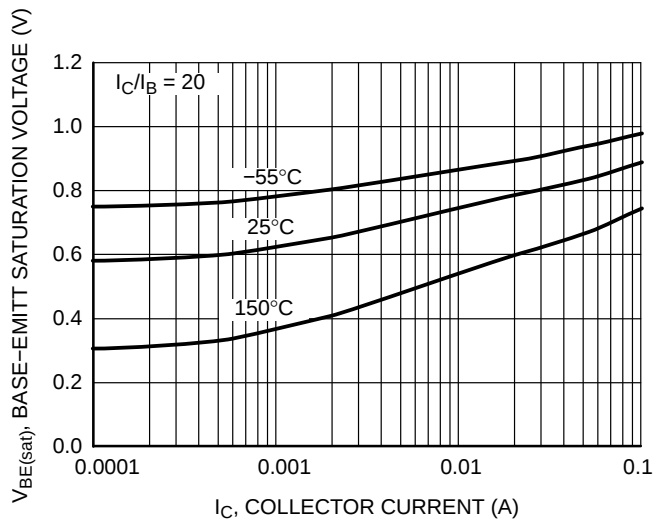


Figure 28. $V_{BE(sat)}$ at $I_C/I_B = 20$

BC846BDW1, BC847BDW1, BC848CDW1

TYPICAL CHARACTERISTICS – BC848CDW1

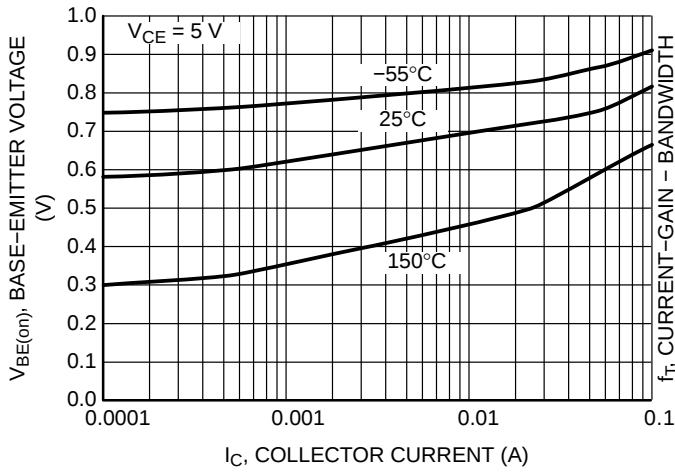


Figure 29. $V_{BE(on)}$ at $V_{CE} = 5\text{ V}$

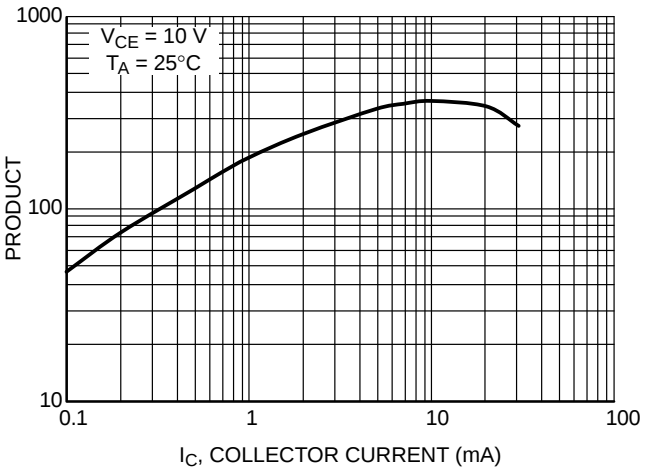


Figure 30. Current - Gain - Bandwidth Product

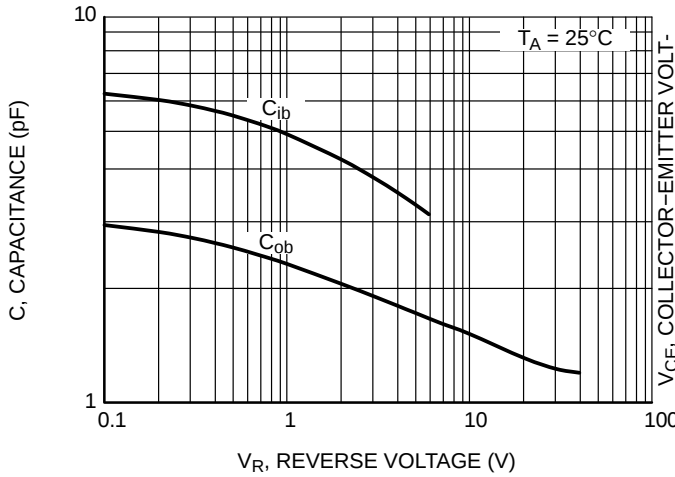


Figure 31. Capacitances

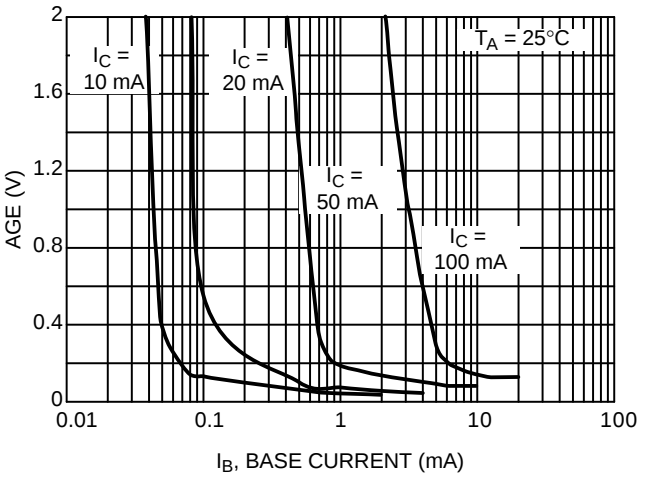


Figure 32. Collector Saturation Region

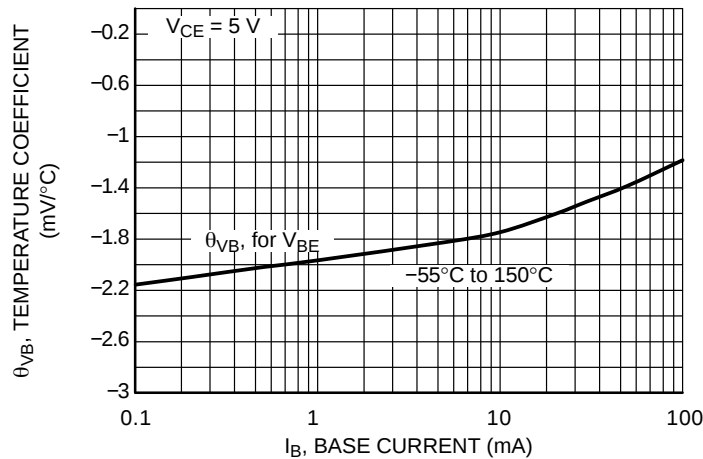


Figure 33. Base-Emitter Temperature Coefficient

BC846BDW1, BC847BDW1, BC848CDW1

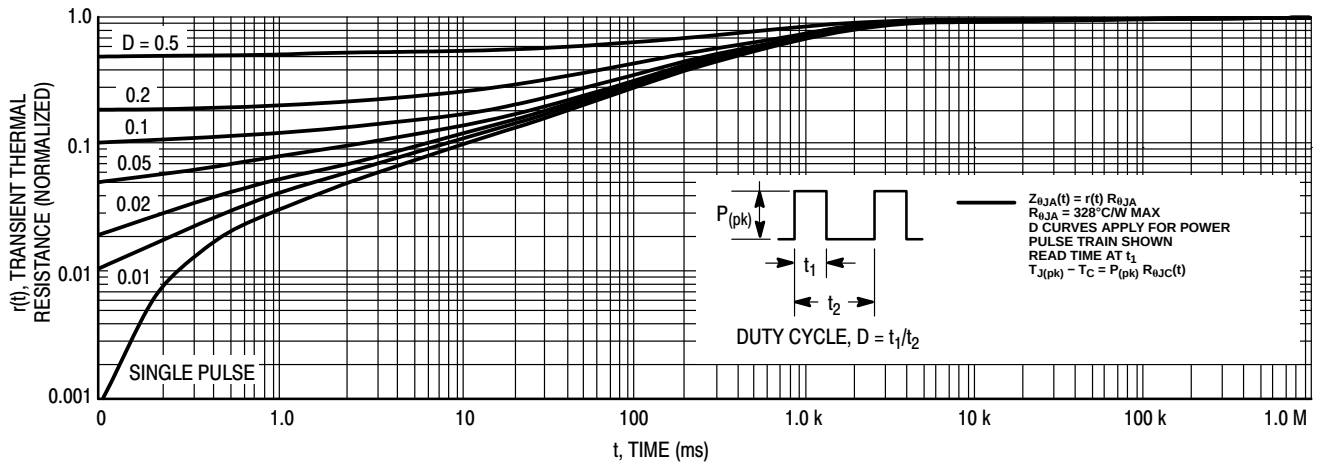


Figure 34. Thermal Response

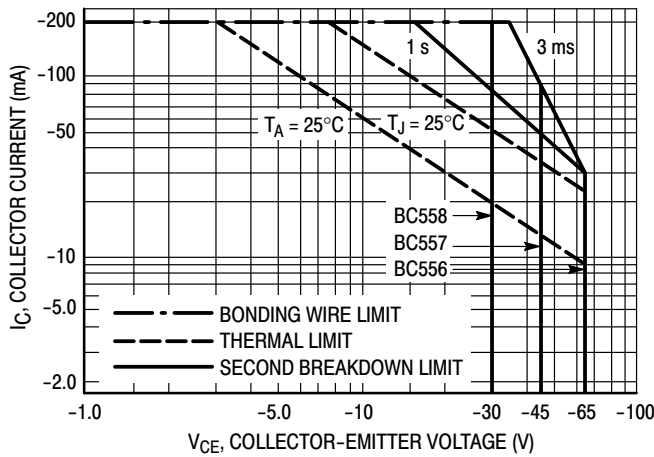


Figure 35. Active Region Safe Operating Area

The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 35 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 34. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

BC846BDW1, BC847BDW1, BC848CDW1

ORDERING INFORMATION

Device	Markings	Package	Shipping [†]
BC846BDW1T1G	1B	SOT-363 (Pb-Free)	3,000 / Tape & Reel
SBC846BDW1T1G*	1B	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC847BDW1T1G	1F	SOT-363 (Pb-Free)	3,000 / Tape & Reel
SBC847BDW1T1G*	1F	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC847BDW1T3G	1F	SOT-363 (Pb-Free)	10,000 / Tape & Reel
SBC847BDW1T3G*	1F	SOT-363 (Pb-Free)	10,000 / Tape & Reel
NSVBC847BDW1T2G*	1F	SOT-363 (Pb-Free)	10,000 / Tape & Reel
BC847CDW1T1G	1G	SOT-363 (Pb-Free)	3,000 / Tape & Reel
SBC847CDW1T1G*	1G	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC848CDW1T1G	1L	SOT-363 (Pb-Free)	3,000 / Tape & Reel
NSVBC848CDW1T1G*	1L	SOT-363 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

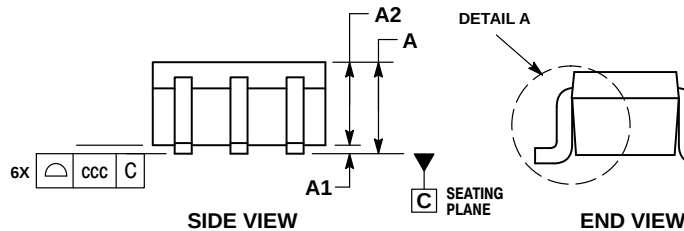
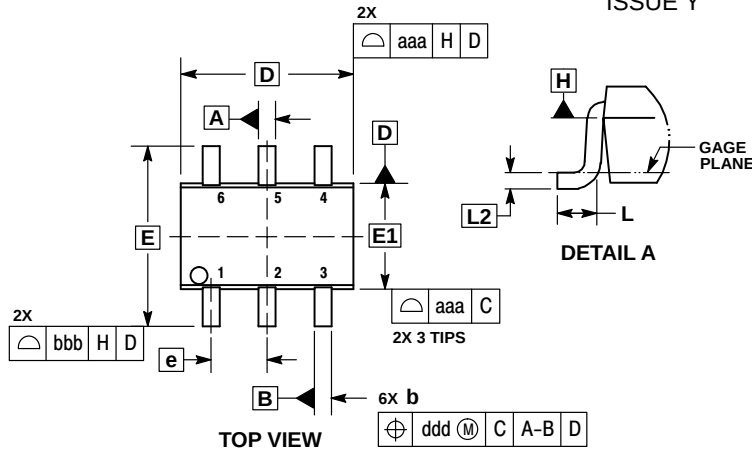
BC846BDW1, BC847BDW1, BC848CDW1

PACKAGE DIMENSIONS

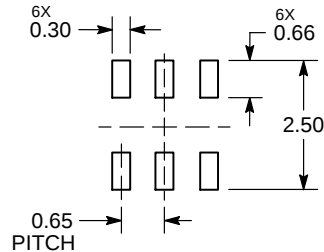
SC-88/SC70-6/SOT-363

CASE 419B-02

ISSUE Y



RECOMMENDED SOLDERING FOOTPRINT*



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

STYLE 1:

1. PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative

BC846BDW1T1/D

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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